



Patent
Attorney's Docket No. 026350-028

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)

Toshiro HIRAMOTO et al)

Application No.: 09/389,321)

Filed: September 3, 1999)

For: MOS TRANSISTOR WITH A)
CONTROLLED THRESHOLD)
VOLTAGE)

Group Art Unit: 2836

Examiner: T. Dickey

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AMENDMENT UNDER 37 C.F.R. §1.111

Assistant Commissioner for Patents
Washington, D.C. 20231

Date: August 7, 2001

Sir:

This Amendment responds to the Office Action dated February 9, 2001 (Paper No.

6). Concurrently filed with this Amendment is a Petition for Extension of Time for a
Three Month Period and a copy of the priority document. Please amend the above-noted
application as follows:

IN THE ABSTRACT:

Please replace the abstract as follows:

A MOS transistor with a controlled threshold voltage includes a SOI which includes
a substrate composed of a semi-conducting material, a single crystal layer composed of a
semi-conducting material and an insulating layer interposed between the substrate and the
single crystal layer. The single crystal layer is formed therein with a source region, a
drain region and a surrounded region surrounded by the source region and the drain